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Arafa et al.

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(54) **INTEGRATED CIRCUIT WITH BORDERLESS CONTACTS**

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(52) **U.S. Cl.** **438/740**; 438/740
(58) **Field of Search** 438/664, 666, 438/683, 674, 704, 740, 970, 634, 675, 655, 221, 437, 291, 910

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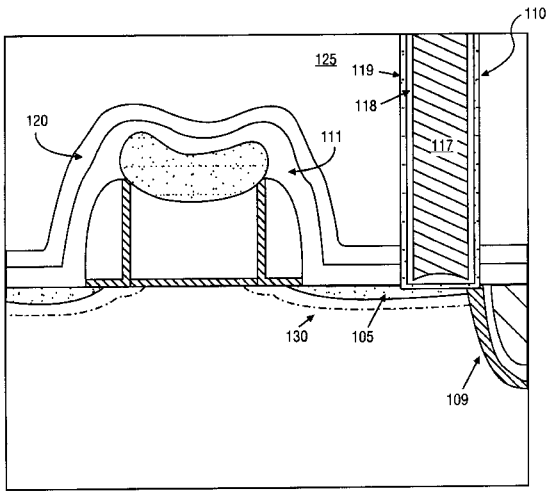
(57) **ABSTRACT**

An integrated circuit comprising a conductive region formed on a semiconductor substrate, a silicate glass layer formed on the conductive region, and an etch stop layer formed on the silicate glass layer. The integrated circuit also includes a borderless contact that is coupled to the conductive region.

10 Claims, 3 Drawing Sheets



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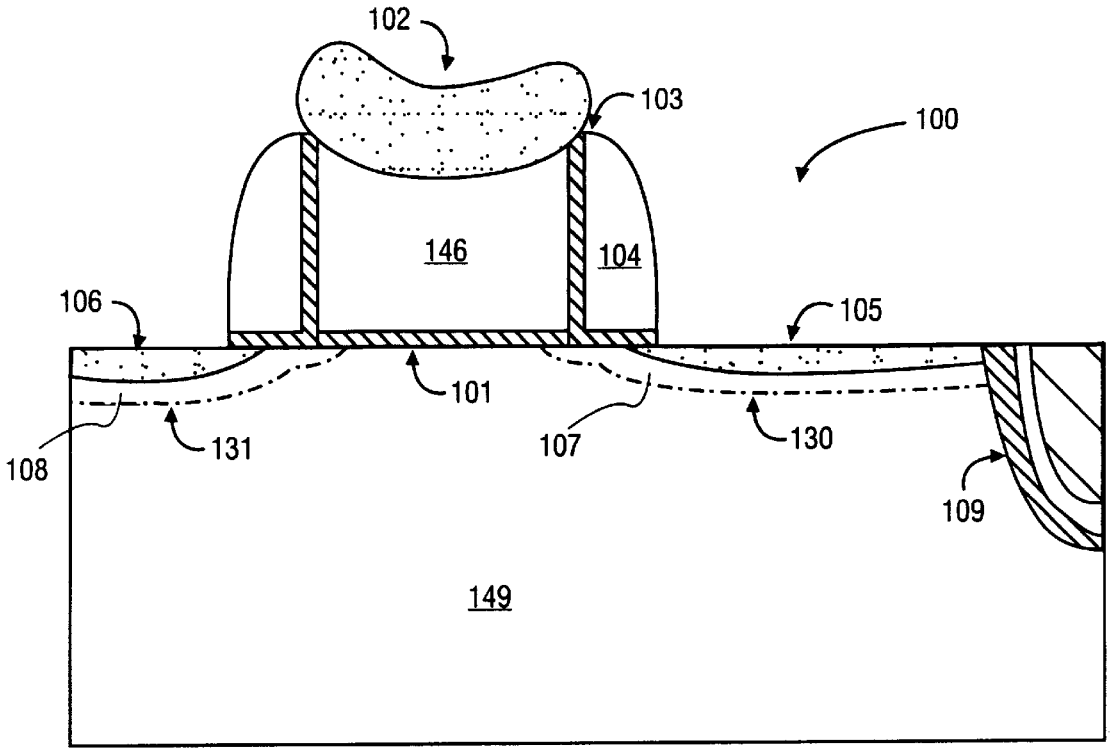

FIGURE 1

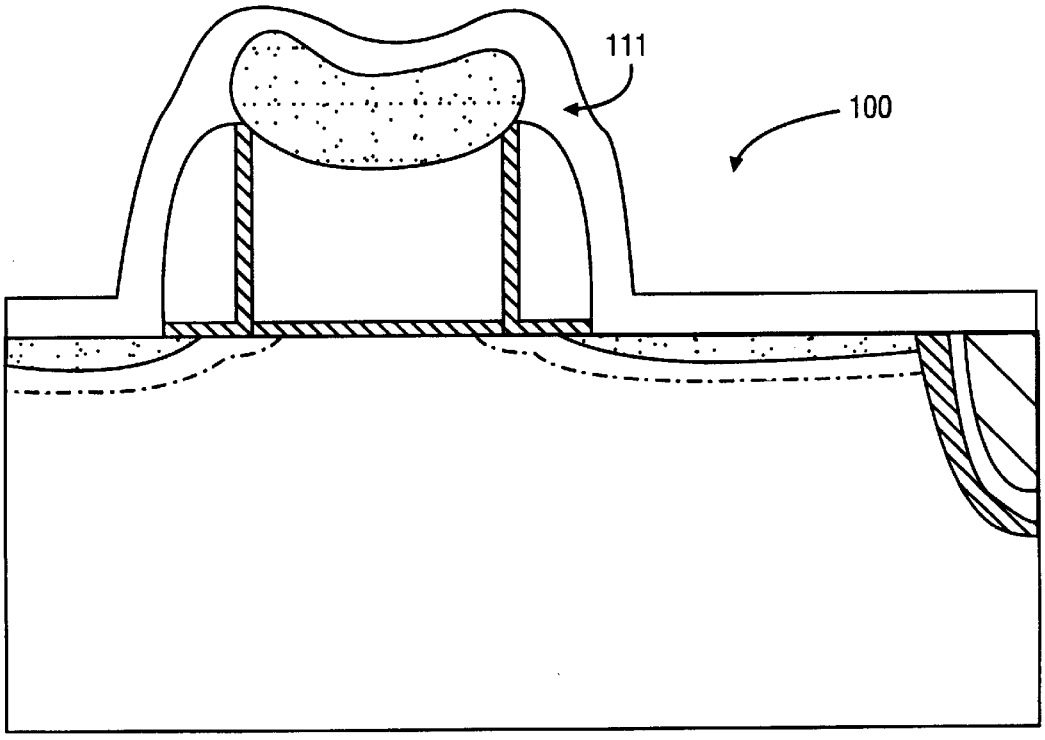

FIGURE 2

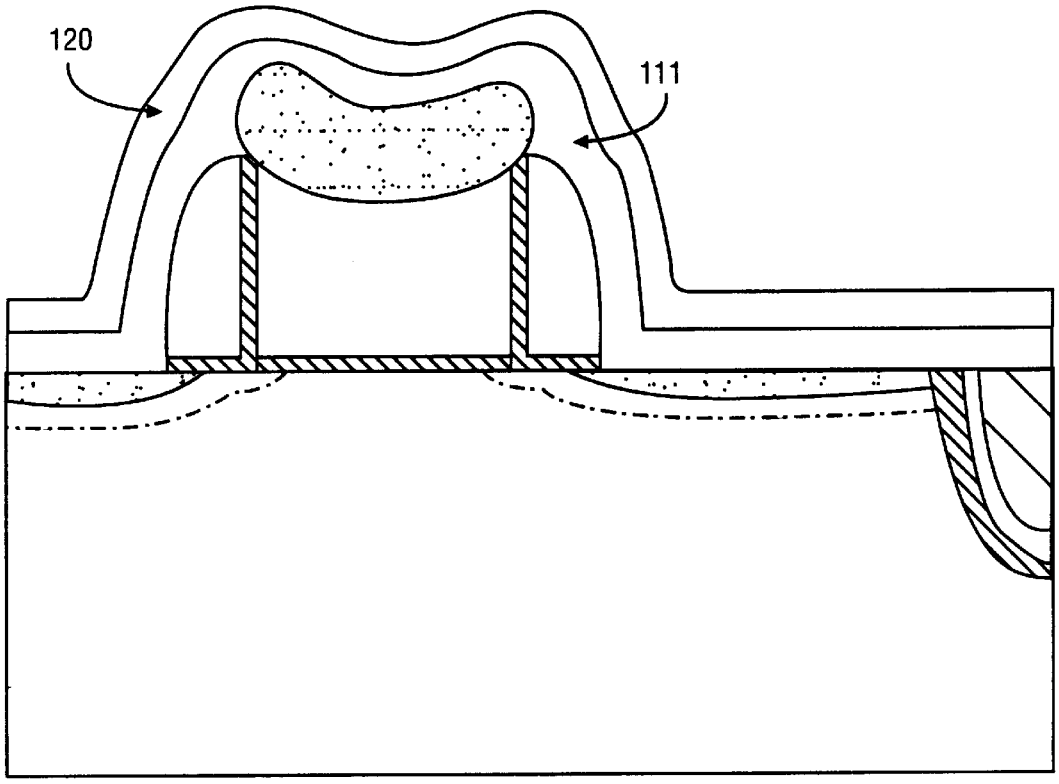

FIGURE 3

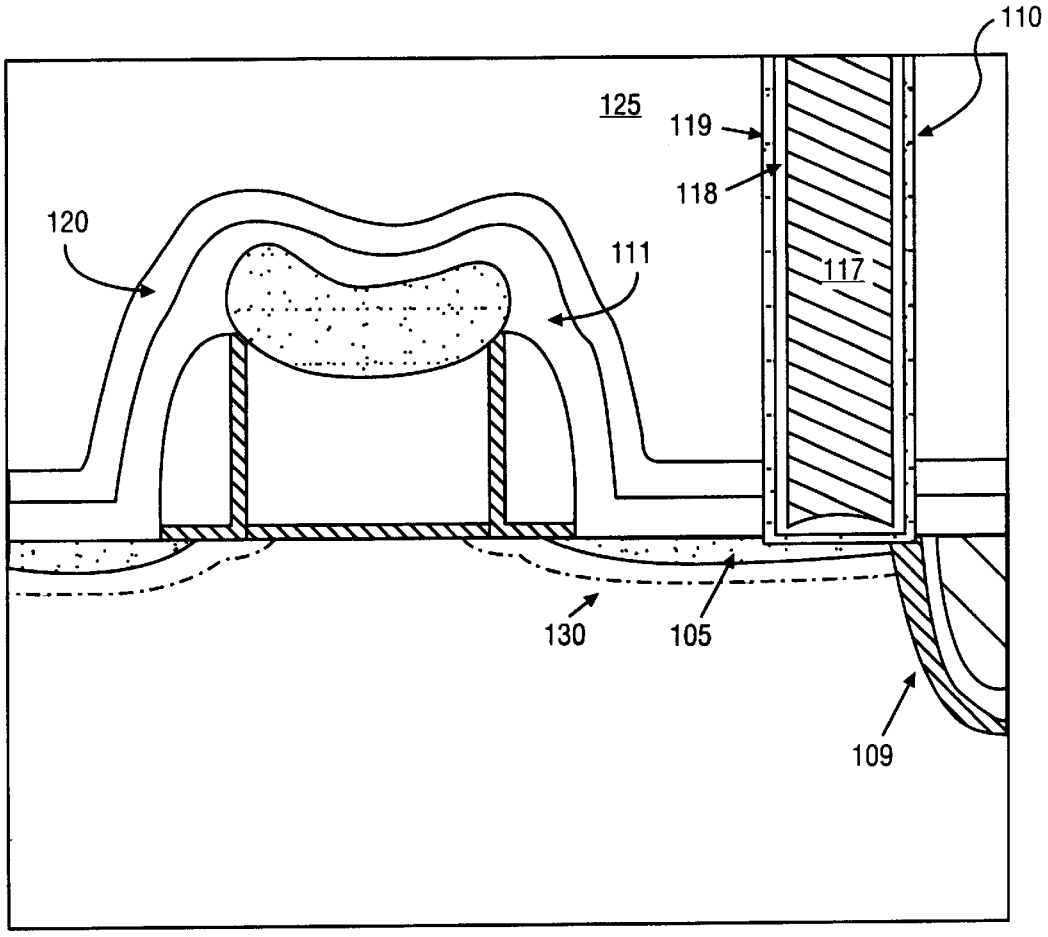

FIGURE 4

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